



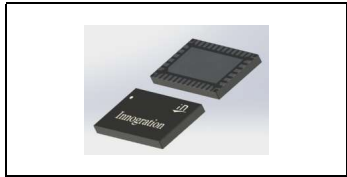
DC-3GHz, 25W, 50V GaN Fully matched PA Module

Description

The SMAV0030-25 is a 25-watt ,single stage integrated Power Amplifier Module, designed for broad band applications, with frequencies from 30MHz to 3GHz. The module is 50 Ω input/output matched and requires minimal external components.

The module implements distributed power amplifier in form of multi chips, housed in cost effective plastic open cavity package, offers a much lower cost than traditional MMIC solutions.

● Vds=50V, Idq=50mA, Pulsed CW (20us, 10%)



Parameter	30MHz	0.5GHz	1.0GHz	1.5GHz	2.0GHz	2.5GHz	3.0GHz	Units
Small signal Gain	20.2	19.0	19.3	18.0	16.7	18.5	17.8	dB
Pout@Pin=31dBm	34.4	38.9	35.0	35.0	34.7	44.6	31.0	W
Gain@Pin=31dBm	14.4	14.9	14.4	14.4	14.4	15.5	13.9	dB
Eff@Pin=31dBm	85	65	59	52	45	56	58	%

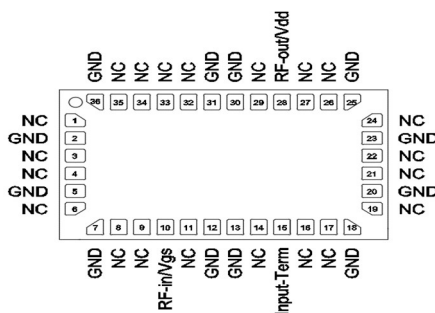
Product Features

- Operating Frequency Range: 30MHz-3GHz
- Operating Drain Voltage: +50 V
- 50 Ω Input/Output
- Psat: ≥25W (Pulsed)
- Small signal gain:>17dB, Power gain:>13dB
- Minimum efficiency:40%
- 6x10 mm Surface Mount Package
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Applications

- Ultra Broadband Amplifiers
- L/S band pulsed power Amplifier
- Test Instrumentation
- EMC Amplifier Drivers
- 2-way Radios

Pin Configuration and Description



Top View



Pin No.	Symbol	Description
28	RFout/Vdd	Transistor 1, Drain Bias & RF Output
10	RFIn/Vgs	Transistor 1, RF Input & Gate Bias
15	Input-Term	Transistor 1, Input 50 ohm term
Others	NC	No connection
2,5,7,12, 13,18,20,23,25, 30, 31,36 Package Base	GND	DC/RF Ground. Must be soldered to EVB ground plane over array of vias for thermal and RF performance. Solder voids under Pkg Base will result in excessive junction temperatures causing permanent damage.

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	200	Vdc
Gate--Source Voltage	V_{GS}	-10 to +2	Vdc
Operating Voltage	V_{DD}	+55	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_c	+150	°C
Operating Junction Temperature	T_j	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case $T_c = 25^\circ\text{C}$, DC test	$R_{\theta JC}$	4	°C/W

Table 3. Electrical Characteristics

Parameter	Condition	Min	Typ	Max	Unit
Frequency Range		30		3000	MHz
Power Gain @ Psat		13			dB
P_{SAT}		25			W
Drain Efficiency @ P_{SAT}		40			%

Unless otherwise noted: $T_A = 25^\circ\text{C}$, $V_{DD} = 50\text{ V}$, Pulse Width=20 us, Duty cycle=10%

Load Mismatch of per Section (On Test Fixture, 50 ohm system): $V_{DD} = 50\text{ V}$, $I_{DQ} = 50\text{ mA}$, $f = 3\text{ GHz}$

VSWR 10:1 at Psat pulse CW Output Power	No Device Degradation
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Reference Circuit of Test Fixture Assembly Diagram

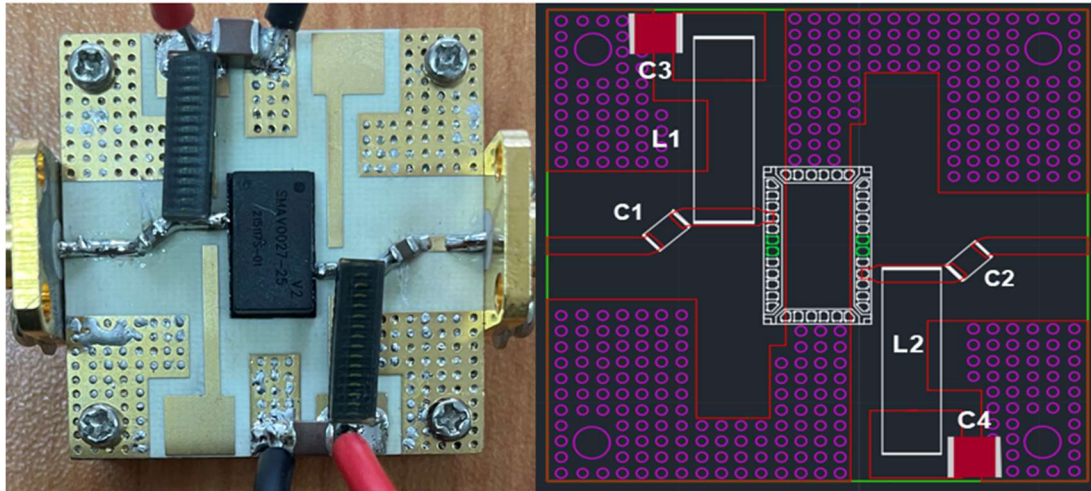


Figure 1. Test Circuit Component Layout

		Part NO.↵	Vendor↵
C3, C4↵	10uF 100V chip Capacitor↵	↵	↵
C1, C2↵	1uF Chip Capacitor↵	↵	ATC↵
L1, L2↵	1.3 uH 4.2A Inductor↵	4310LC-132KEC↵	Coilcraft↵
PCB↵	R04350B, 20mil, Er=3.48↵	↵	MTL↵

TYPICAL CHARACTERISTICS

Figure 2. Network analyzer output S11/S21 (Pin=0dBm)

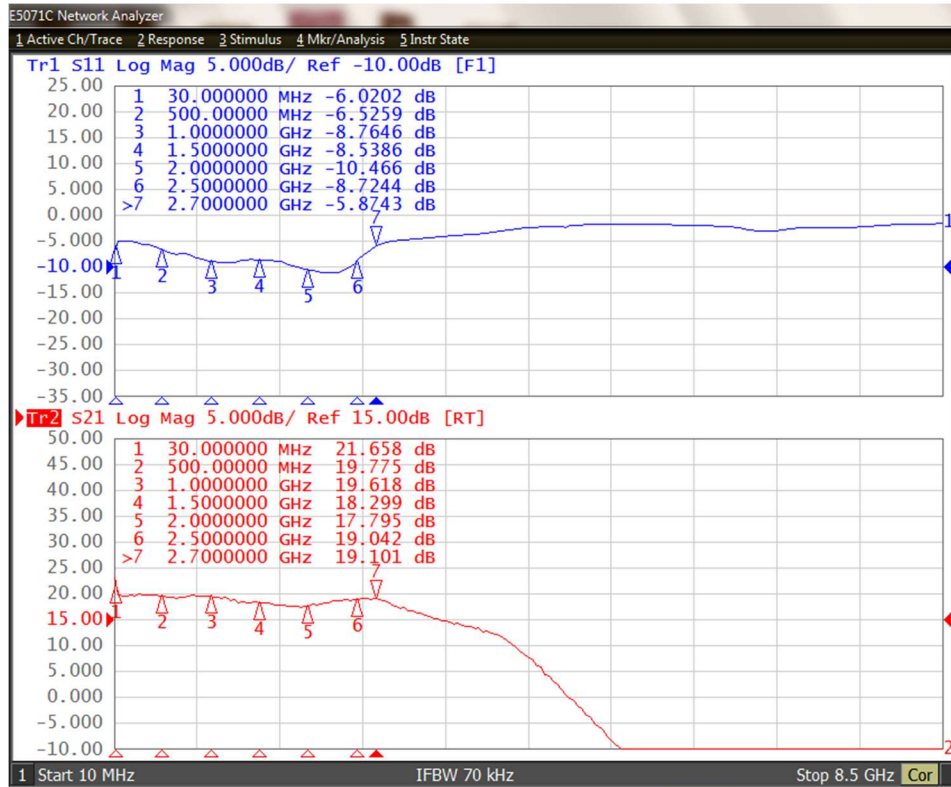
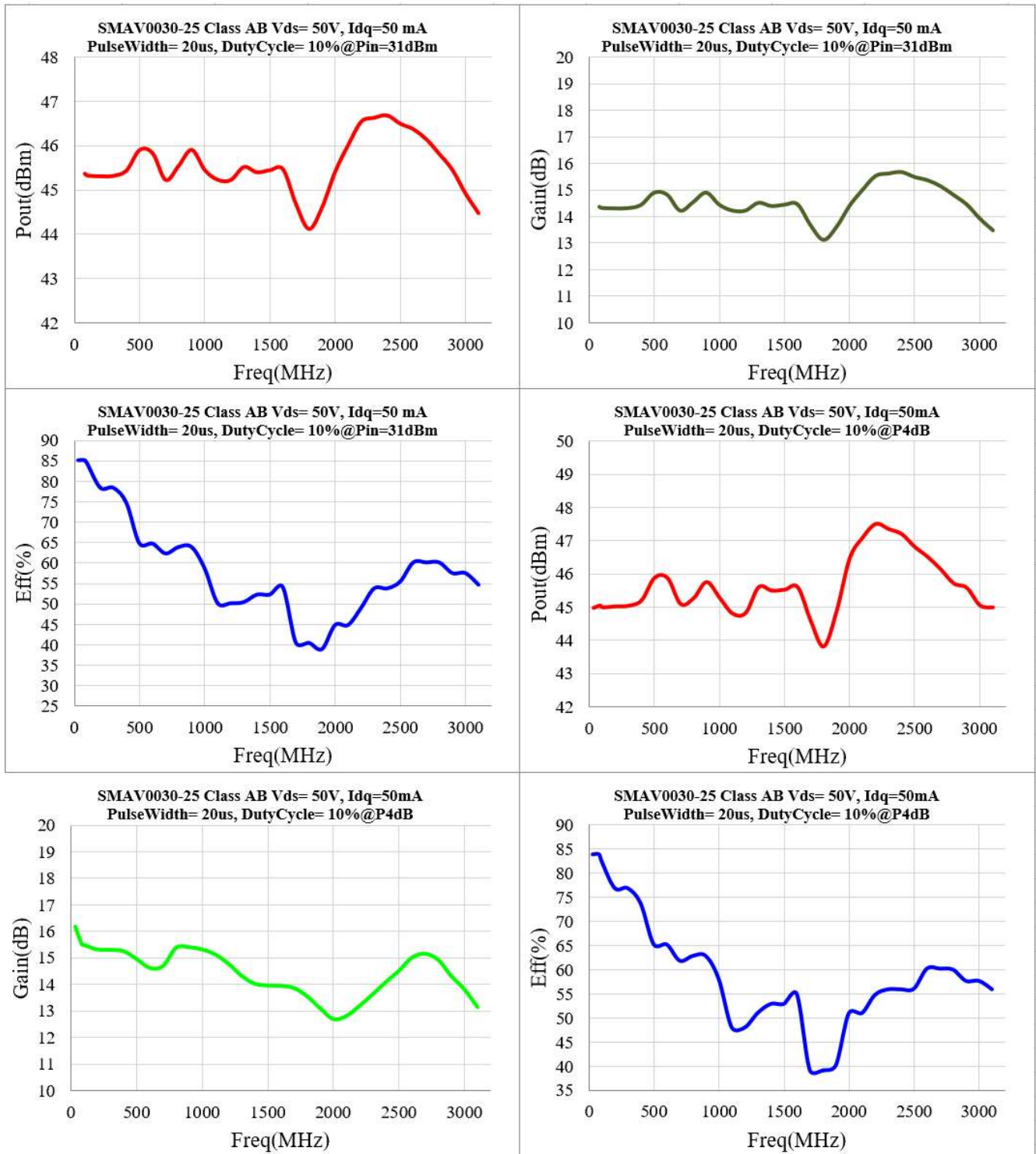


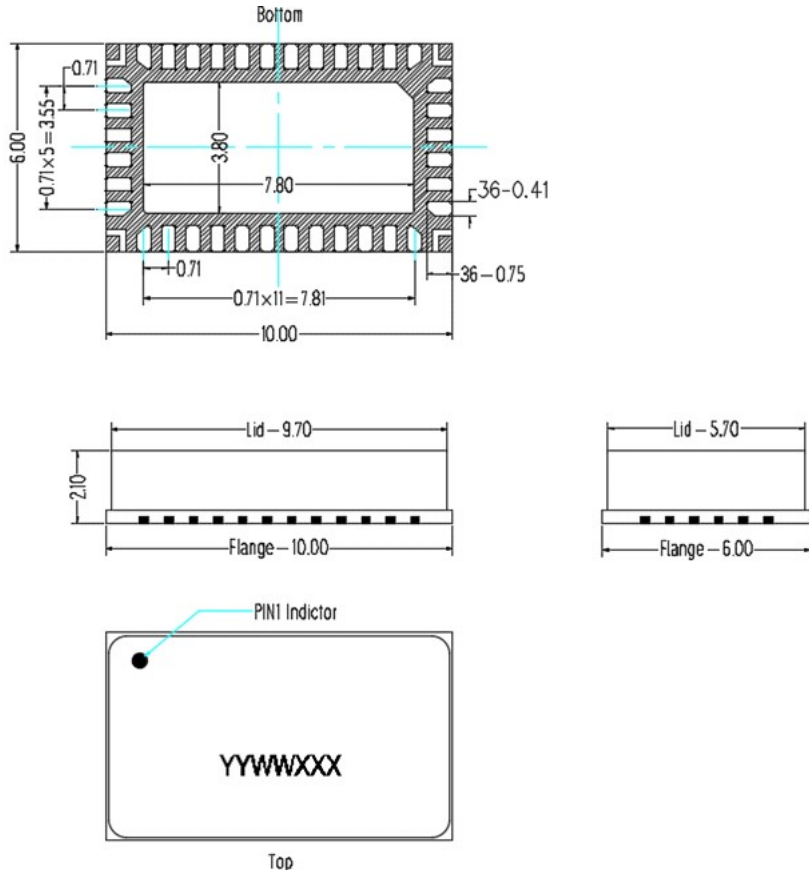


Figure 3. Pout, Power Gain and, efficiency vs. Frequency @Pin=31dBm



Package Dimensions

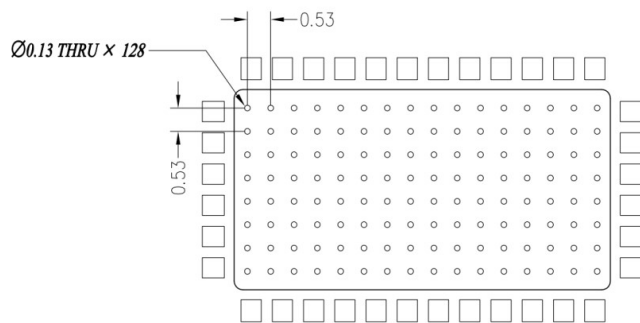
10*6 Plastic Package



Notes:

1. All dimensions are in mm;
2. The tolerances unless specified are ± 0.2 mm.

Mounting Footprint Pattern



Notes:

1. All dimensions are in mm;
2. Vias are required under the backside paddle of this device for proper RF/DC grounding and thermal dissipation. ALL vias are PTH to ground.



Revision history

Table 6. Document revision history

Date	Revision	Datasheet Status
2022/12/9	Rev 1.0	Production Datasheet

Application data based on ZHH-21-22 (3*1.2)

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